

an organic resin film provided over said thin film transistor and said interlayer insulating film; and

a pixel electrode formed over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film,

wherein said interlayer insulating film is located between said organic resin film and said channel region of the thin film transistor, and

wherein said thin film transistor comprises silicon and exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

10. (Amended) An electro-optical device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising source, drain and channel regions;

an interlayer insulating film comprising an inorganic material formed on said thin film transistor;

an organic resin film provided over said thin film transistor and said interlayer insulating film; and

a pixel electrode formed over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film,

wherein said interlayer insulating film is located between said organic resin film and at least said channel region of the thin film transistor,

wherein said thin film transistor comprises silicon and exhibits a peak of

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19. (Amended) An electro-optical device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

a crystalline semiconductor layer having source, drain and channel regions;

a gate insulating layer adjacent to said channel region; and

a gate electrode adjacent to said channel region;

an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said thin film transistor and said interlayer insulating film;

wherein said interlayer insulating film is located between said organic resin film and at least said channel region of the thin film transistor,

wherein said thin film transistor comprises silicon and exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

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32. (Amended) An electro-optical device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

a crystalline semiconductor layer having source, drain and channel regions;

a gate insulating layer adjacent to said channel region;

an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said thin film transistor and said interlayer insulating film;

wherein said interlayer insulating film is located between said organic resin film and at least said channel region of the thin film transistor, and

wherein said semiconductor layer comprises silicon and exhibits a peak of Raman spectra, displaced from 522 cm^{-1} to the lower frequency direction.

45. (Amended) An electro-optical device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least an n-channel thin film transistor and at least a p-channel thin film transistor both formed over said first substrate, each of said n-channel and p-channel thin film transistors comprising:

a crystalline semiconductor layer having source, drain and channel regions;

a gate insulating layer adjacent to said channel region; and

a gate electrode adjacent to said channel region;

an interlayer insulating film comprising an inorganic material formed on said thin film transistor; and

an organic resin film provided over said thin film transistor and said interlayer insulating film;

wherein said interlayer insulating film is located between said organic resin film and at least said channel region of the thin film transistor,

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contd
A5 wherein said thin film transistor comprises silicon and exhibits a peak of Raman spectra, displaced from a peak of single crystalline silicon to the lower frequency direction.

Please add new claims 68-76 as follows:

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B8 68. An electro-optical device comprising:

a first substrate having an insulating surface;

a second substrate opposing said first substrate;

at least one thin film transistor formed on said insulating surface, said thin film transistor comprising:

a crystalline semiconductor layer having source, drain and channel regions;

an interlayer insulating film comprising an inorganic material formed on said

A6 thin film transistor; and

an organic resin film provided over said thin film transistor and said interlayer insulating film;

a pixel electrode provided over said organic resin film and connected to said thin film transistor through an opening provided in said organic resin film;

wherein said interlayer insulating film is located between said organic resin

70. A device according to claim 68 wherein said inorganic material comprises silicon oxide.

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71. A device according to claim 68 wherein said channel region comprises a material selected from the group consisting of silicon, germanium and a combination thereof.

72. A device according to claim 68 wherein said interlayer insulating film is 0.2 to 0.6 μm thick.

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73. A device according to claim 68 consisting of 640 x 480 pixels arranged in a matrix form.

74. A device according to claim 68 consisting of 1260 x 960 pixels arranged in a matrix form.

75. A device according to claim 68, wherein said organic resin film comprises polyimide.

76. A device according to claim 68, wherein said channel region comprises boron at concentration in a range of $1 \times 10^{15} - 1 \times 10^{18} \text{ cm}^{-3}$.

REMARKS

This application has been amended to include the phrase "to the lower frequency direction" in claims 1, 10, 19, 32 and 45 and to add new claims 68-76 to add additional protection to which application is entitled.